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Email & Skype: info@chipsmall.com Web: www.chipsmall.com
Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China

Product Summary

BV_{DSS}	$R_{DS(ON)}$ max	I_D max T_A = +25°C
30V	20.5mΩ @ V_{GS} = 10V	8.3A
	30mΩ @ V_{GS} = 4.5V	7.4A

Features and Benefits

- 0.6mm Profile – Ideal for Low Profile Applications
- PCB Footprint of 4mm^2
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Description and Applications

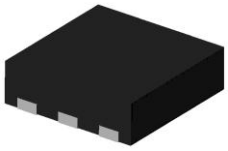
This new generation MOSFET has been designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- General Purpose Interfacing Switch
- Power Management Functions

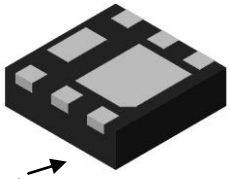
Mechanical Data

- Case: U-DFN2020-6 (Type F)
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – NiPdAu over Copper leadframe. Solderable per MIL-STD-202, Method 208 e4
- Weight: 0.0065 grams (Approximate)

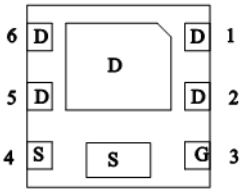
U-DFN2020-6
(Type F)



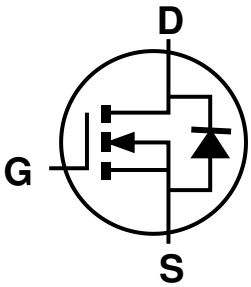
Top View



Bottom View



Pin Out
Bottom View



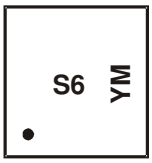
Internal Schematic

Ordering Information (Note 4)

Part Number	Case	Packaging
DMN3025LFDF-7	U-DFN2020-6 (Type F)	3,000/Tape & Reel
DMN3025LFDF-13	U-DFN2020-6 (Type F)	10,000/Tape & Reel

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
2. See http://www.diodes.com/quality/lead_free.htmlfor more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



S6 = Product Type Marking Code
YM = Date Code Marking
Y = Year (ex: D = 2016)
M = Month (ex: 9 = September)

Date Code Key

Year	2016	2017	2018	2019	2020	2021	2022	2023
Code	D	E	F	G	H	I	J	K

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

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Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V_{DSS}	30	V
Gate-Source Voltage			V_{GSS}	±20	V
Continuous Drain Current (Note 6) V_{GS} = 10V	Steady State	T_A = +25°C T_A = +70°C	I_D	8.3 6.6	A
	t<10s	T_A = +25°C T_A = +70°C	I_D	9.9 7.9	A
Maximum Continuous Body Diode Forward Current (Note 6)			I_S	3	A
Pulsed Drain Current (10µs pulse, duty cycle = 1%)			I_{DM}	40	A
Avalanche Current (L = 0.1mH) (Note 7)			I_{AS}	15	A
Avalanche Energy (L = 0.1mH) (Note 7)			E_{AS}	11	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)	T_A = +25°C	P_D	0.66	W
	T_A = +70°C		0.42	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	173	°C/W
	t<10s		133	
Total Power Dissipation (Note 6)	T_A = +25°C	P_D	2.1	W
	T_A = +70°C		1.3	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	62	°C/W
	t<10s		43	
Thermal Resistance, Junction to Case (Note 6)	Steady State	$R_{\theta JC}$	9.4	°C/W
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV_{DSS}	30	-	-	V	V_{GS} = 0V, I_D = 250µA
Zero Gate Voltage Drain Current	I_{DSS}	-	-	1	µA	V_{DS} = 30V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	-	-	±100	nA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	$V_{GS(TH)}$	1.0	-	2.0	V	V_{DS} = V_{GS}, I_D = 250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	-	-	20.5	mΩ	V_{GS} = 10V, I_D = 7A
		-	-	30		V_{GS} = 4.5V, I_D = 7A
Diode Forward Voltage	V_{SD}	-	0.70	1.0	V	V_{GS} = 0V, I_S = 1A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C_{iss}	-	641	-	pF	V_{DS} = 15V, V_{GS} = 0V, f = 1.0MHz
Output Capacitance	C_{oss}	-	66	-		
Reverse Transfer Capacitance	C_{rss}	-	50	-		
Gate Resistance	R_g	-	2.2	-	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz
Total Gate Charge (V_{GS} = 4.5V)	Q_g	-	6	-	nC	V_{DS} = 15V, I_D = 10A
Total Gate Charge (V_{GS} = 10V)	Q_g	-	13.2	-		
Gate-Source Charge	Q_{gs}	-	1.7	-		
Gate-Drain Charge	Q_{gd}	-	2.2	-		
Turn-On Delay Time	$t_{D(ON)}$	-	3.3	-	ns	V_{DD} = 15V, V_{GS} = 10V, R_G = 6Ω, I_D = 1A
Turn-On Rise Time	t_R	-	4.4	-		
Turn-Off Delay Time	$t_{D(OFF)}$	-	22.3	-		
Turn-Off Fall Time	t_F	-	5.3	-		
Reverse Recovery Time	t_{RR}	-	11.4	-	ns	I_F = 11A, di/dt = 100A/µs
Reverse Recovery Charge	Q_{RR}	-	8.2	-	nC	I_F = 11A, di/dt = 100A/µs

Notes:
5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
7. I_{AS} and E_{AS} rating are based on low frequency and duty cycles to keep T_J = +25°C.
8. Short duration pulse test used to minimize self-heating effect.
9. Guaranteed by design. Not subject to product testing.

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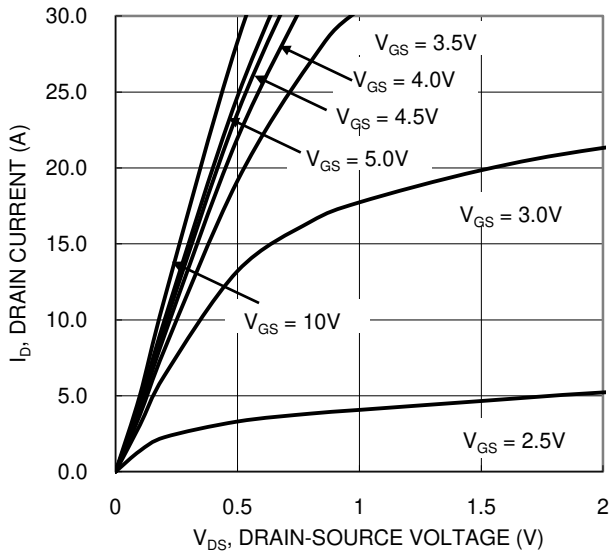

Figure 1. Typical Output Characteristic

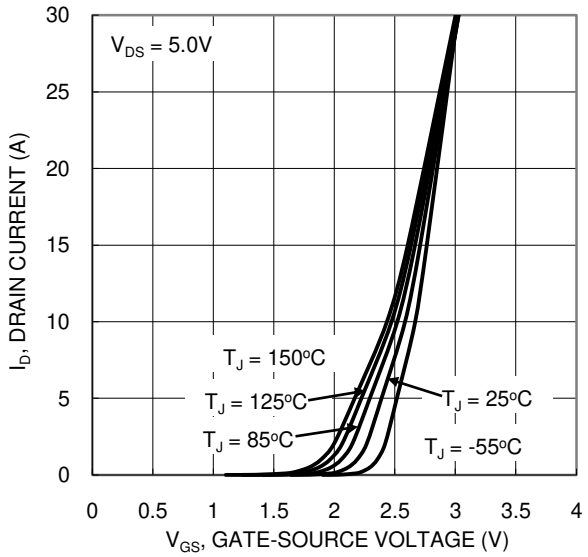

Figure 2. Typical Transfer Characteristic

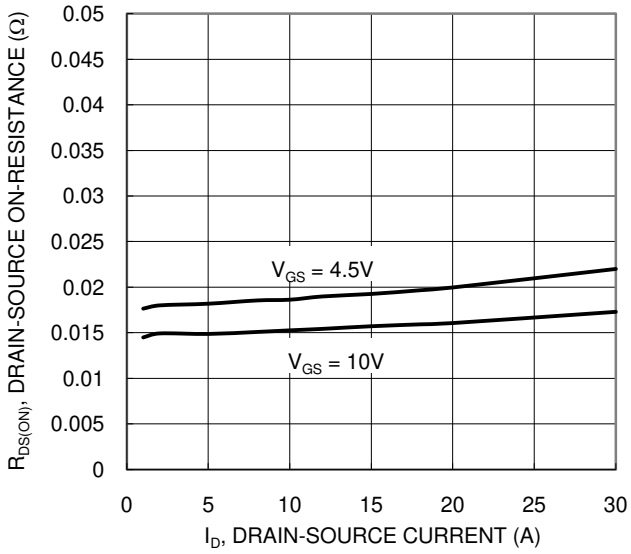

Figure 3. Typical On-Resistance vs Drain Current and Gate Voltage

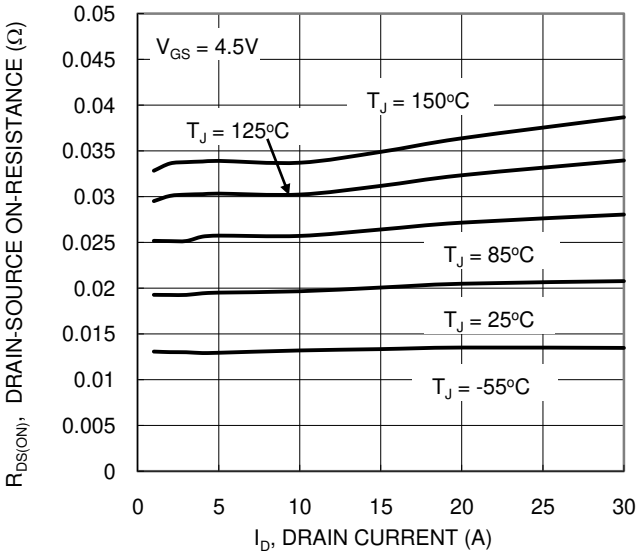

Figure 4. Typical On-Resistance vs Drain Current and Temperature

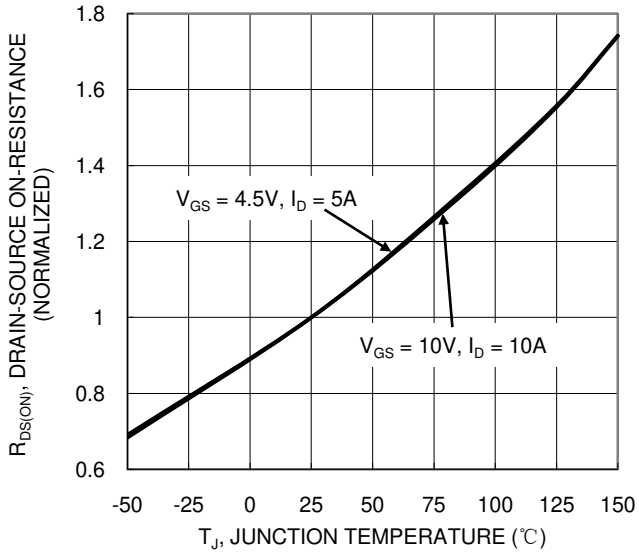

Figure 5. On-Resistance Variation with Temperature

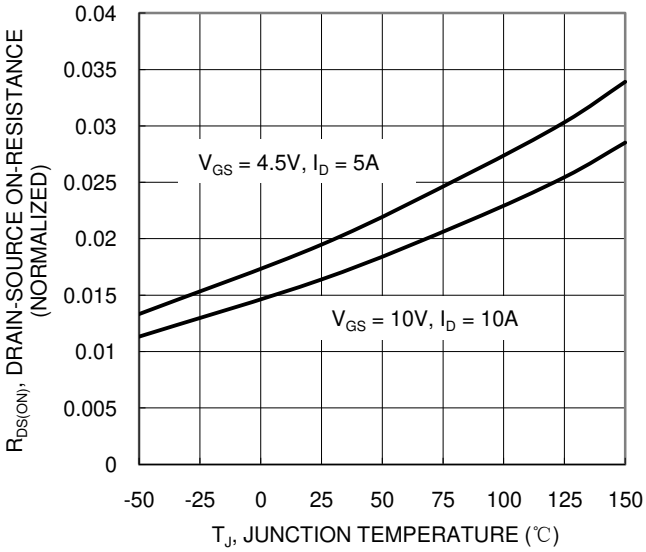

Figure 6.On-Resistance Variation with Temperature

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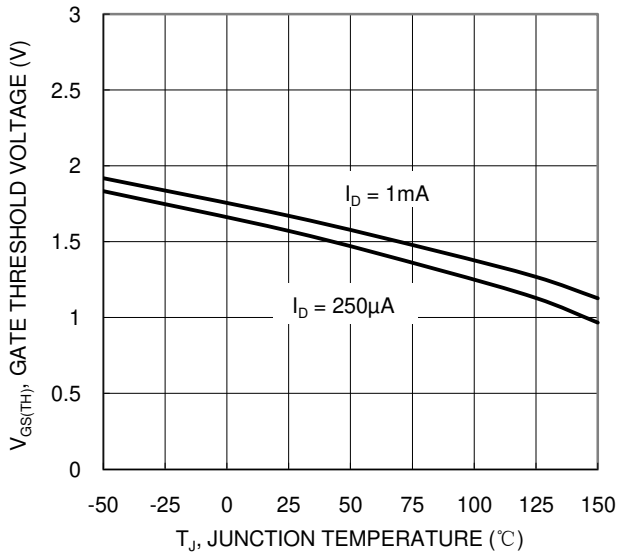

Figure 7. Gate Threshold Variation vs Junction Temperature

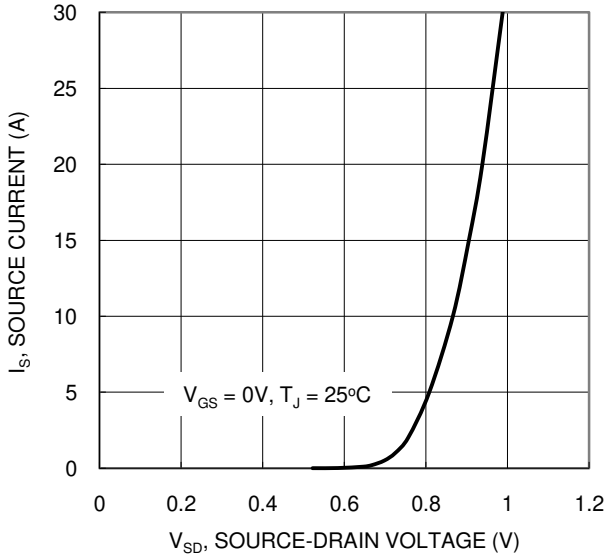

Figure 8. Diode Forward Voltage vs. Current

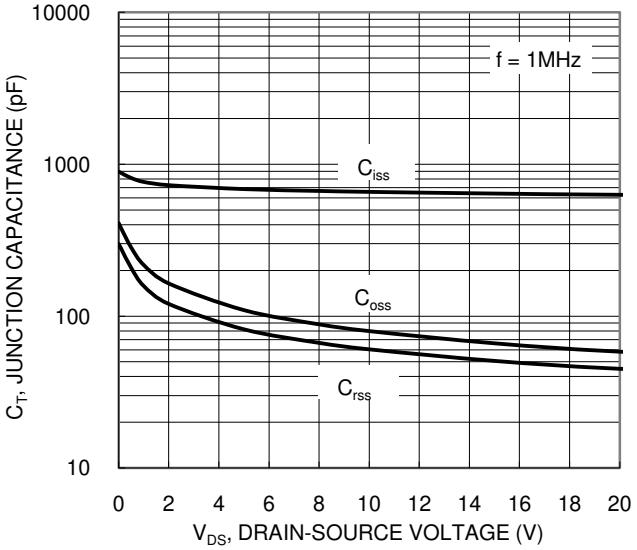

Figure 9. Typical Junction Capacitance

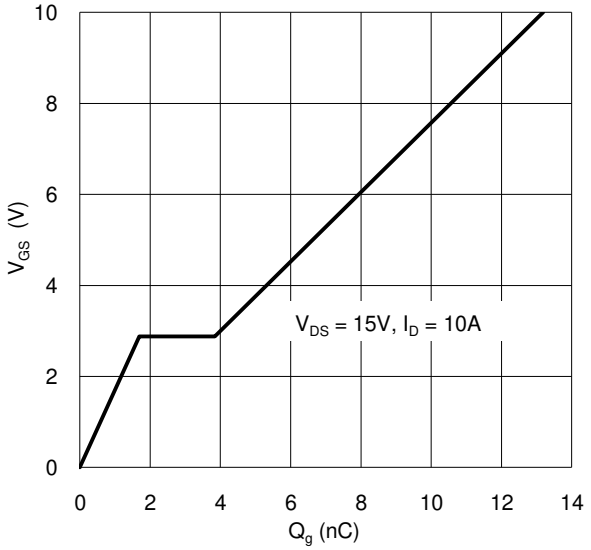

Figure 10. Gate Charge

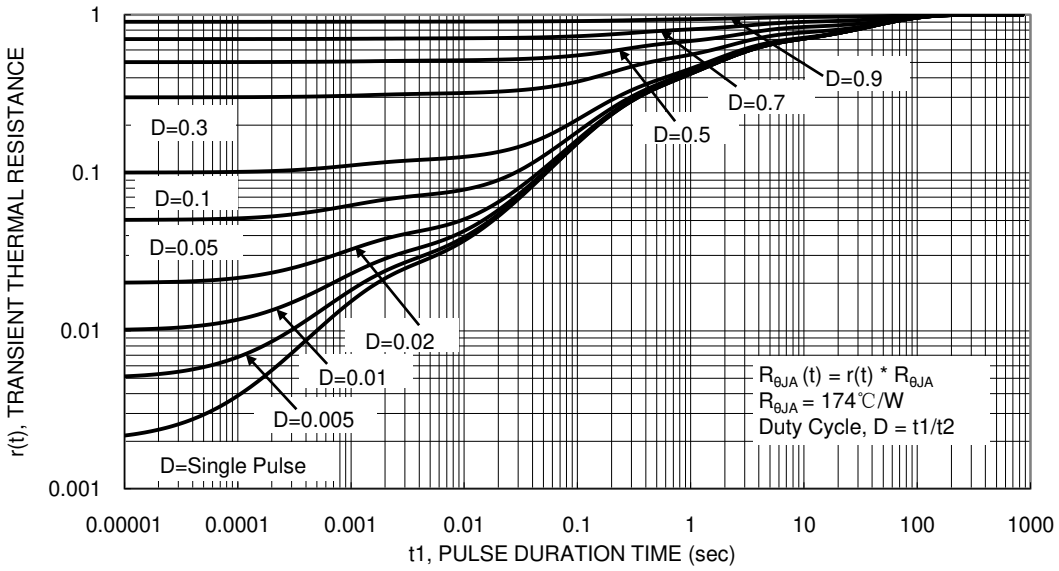

Figure 11. Transient Thermal Resistance

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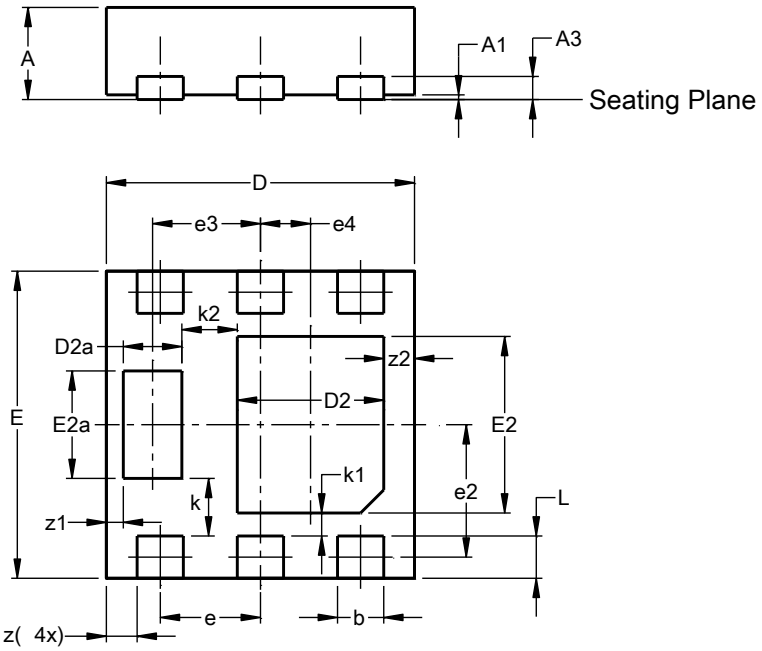
Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type F)

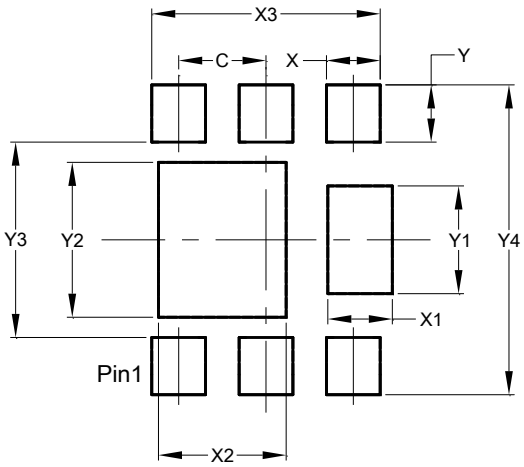


U-DFN2020-6 (Type F)			
Dim	**Min**	**Max**	**Typ**
A	0.57	0.63	0.60
A1	0.00	0.05	0.03
A3	-	-	0.15
b	0.25	0.35	0.30
D	1.95	2.05	2.00
D2	0.85	1.05	0.95
D2a	0.33	0.43	0.38
E	1.95	2.05	2.00
E2	1.05	1.25	1.15
E2a	0.65	0.75	0.70
e	0.65 BSC		
e2	0.863 BSC		
e3	0.70 BSC		
e4	0.325 BSC		
k	0.37 BSC		
k1	0.15 BSC		
k2	0.36 BSC		
L	0.225	0.325	0.275
z	0.20 BSC		
z1	0.110 BSC		
z2	0.20 BSC		
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type F)



Dimensions	Value (in mm)
C	0.650
X	0.400
X1	0.480
X2	0.950
X3	1.700
Y	0.425
Y1	0.800
Y2	1.150
Y3	1.450
Y4	2.300

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